

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	2	"6693021".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:25
S3	7	("4727047" "5843227" "5846609" "6087681" "6096130" "6156581" "6225650").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/24 14:40
S5	25	"1041610"	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/24 14:46
S6	798	molnar.in.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/24 14:58
S4	132	(gaas or gallium near2 arsenide) near10 substrate and (gan or gallium near2 nitride) near10 (elo or lateral near2 overgrow\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/24 14:58
S8	2	"9641906"	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/24 15:01
S7	3	molnar.in. and remov\$5 near2 substrate	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/24 15:01
S9	5	"6087681".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:10
S11	352	epitax\$6 near10 later\$6 near15 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:11
S10	5	"5838029".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:11
S12	184	epitax\$6 near10 later\$6 near15 nitride and (gaas or gallium near2 arsenide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:12

S13	107	epitax\$6 near10 later\$6 near15 nitride and (gaas or gallium near2 arsenide) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:15
S15	408	epitax\$6 near10 later\$6 near15 (gallium near2 nitride or gan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:16
S14	154	epitax\$6 near10 later\$6 near15 gallium near2 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:16
S16	14	epitax\$6 near10 later\$6 near15 (gallium near2 nitride or gan) and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:53
S17	8	overgrow\$5 near10 (gallium near2 nitride or gan) and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 17:10
S18	2343	(akira near2 usui or haruo near2 sunakawa or akira near2 sakai or atsushi near2 yamaguchi).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 17:11
S19	68	(akira near2 usui or haruo near2 sunakawa or akira near2 sakai or atsushi near2 yamaguchi).in. and (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 17:12
S20	33	(akira near2 usui or haruo near2 sunakawa or akira near2 sakai or atsushi near2 yamaguchi).in. and (gan or gallium near2 nitride) and (stripe mask\$4 or pattern\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 18:01
S21	38	(akira near2 usui or haruo near2 sunakawa or akira near2 sakai or atsushi near2 yamaguchi).in. and (stripe mask\$4 or pattern\$6) near15 direction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 18:02
S25	21	(stripe mask\$4 or pattern\$6) near15 direction and (gan or gallium near2 nitride) near10 epitax\$7 and (gaas or gallium near2 arsenide) near10 substrate and @py<"2001"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 18:03

S24	195	(stripe mask\$4 or pattern\$6) near15 direction and (gan or gallium near2 nitride) near10 epitax\$7 and (gaas or gallium near2 arsenide) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 18:03
S23	418	(stripe mask\$4 or pattern\$6) near15 direction and (gan or gallium near2 nitride) and (gaas or gallium near2 arsenide) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 18:03
S22	1322	(stripe mask\$4 or pattern\$6) near15 direction and (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 18:03
S27	371	(elo or epitax\$6 near2 later\$6 near2 overgrow\$6) near15 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:19
S26	1399	elo or epitax\$6 near2 later\$6 near2 overgrow\$6 near15 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:19
S1	2	"20040089222".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:19
S29	2	"6071643".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:41
S28	158	(elo or epitax\$6 near2 later\$6 near2 overgrow\$6) near15 (gan or gallium near2 nitride) and (gaas or gallium near2 arsenide) near10 (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:08
S30	2	"6103604".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:32
S31	5	(aln or aluminum near2 nitride) near5 buffer near10 (Hvpe or (halide or hydride) near2 vapor near2 phase)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:35

S33	206	(aln or aluminum near2 nitride) same (Hvpe or (halide or hydride) near2 vapor near2 phase)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:36
S32	53	(aln or aluminum near2 nitride) near10 (Hvpe or (halide or hydride) near2 vapor near2 phase)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:36
S34	6	(aln or aluminum near2 nitride) same (Hvpe or (halide or hydride) near2 vapor near2 phase) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:38
S36	39	(gan or gallium near2 nitride) same (Hvpe or (halide or hydride) near2 vapor near2 phase) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:40
S35	31	(gan or gallium near2 nitride) same (Hvpe or (halide or hydride) near10 buffer near2 vapor near2 phase) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:40
S37	54	(hvpe or (halide or hydride) near vapor near2 phase) near15 (movpe or metal near2 organ\$6 near2 vapor near2 phase) near20 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 18:51
S38	2	"5770887".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 12:17
S39	1445	(elo or epitax\$6 near2 lateral\$4 or elog) and direction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 12:20
S41	54	S40 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 12:21
S40	649	(elo or epitax\$6 near2 lateral\$4 or elog) same ("ii-v" or gaas or gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 12:23

S42	522	(elo or epitax\$6 near2 lateral\$4 or elog) same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:24
S43	302	(gan or gallium near2 nitride) near10 (slic\$5 or cut\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:25
S44	41	(gan or gallium near2 nitride) near10 (slic\$5 or cut\$6) and @py<"2001"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:28
S46	1909	molnar.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:30
S45	38	(gan or gallium near2 nitride) near10 ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:30
S47	6	molnar.in. and remov\$5 near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:31
S48	318	(gan or gallium near2 nitride) near10 cleav\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:32
S50	348	(gan or gallium near2 nitride) near15 substrate near10 (cut\$5 or cleav\$6 or slic\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:38
S49	24	(gan or gallium near2 nitride) near10 cleav\$6 and @py<"2001"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:38
S51	35	(gan or gallium near2 nitride) near15 substrate near10 (cut\$5 or cleav\$6 or slic\$5) and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:43

S52	1	(gan or gallium near2 nitride) near20 ingot and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:53
S53	320	(gan or gallium near2 nitride or group near3 nitride) same substrate near10 (gaas or gallium near2 arsenide) near10 (sapphire or "al.sub.2o.sub.3") near10 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:55
S55	5	"5838029".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:23
S54	3	(gan or gallium near2 nitride or group near3 nitride) same substrate near10 (gaas or gallium near2 arsenide) near10 (sapphire or "al.sub.2o.sub.3") near10 (sic or silicon near2 carbide) and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:23
S58	175	mask near10 pattern\$6 near10 pitch near10 direction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:42
S57	1329	mask near10 pattern\$6 near10 pitch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:42
S56	5	"5838029".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:42
S59	7	mask near10 pattern\$6 near10 pitch near10 direction near10 parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:58
S60	67	(hype or (halide or hydride) near4 (vapor near2 phase near2 epitax\$4)) near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:00

S61	407	(movpe or metal near2 organ\$6) near10 (hvpe or (halide or hydride) near10 (vapor near2 epitax\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:02
S64	28	(gan or gallium near2 nitride) near16 cleav\$6 and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:19
S63	367	(gan or gallium near2 nitride) near16 cleav\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:19
S62	70	(movpe or metal near2 organ\$6) near10 (hvpe or (halide or hydride) near10 (vapor near2 epitax\$4)) near16 (gan or aln or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:19
S67	125	(gan or gallium near2 nitride) near16 sheet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:20
S66	4	(gan or gallium near2 nitride) near16 sheet near10 ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:20
S65	3	(gan or gallium near2 nitride) near16 cleav\$6 near10 sheet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:20
S68	641	(gan or gallium near2 nitride) near16 (slic\$5 or cut\$6 or cleav\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:21
S69	92	(gan or gallium near2 nitride) near16 (slic\$5 or cut\$6 or cleav\$5) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:29
S75	300	ingot near10 (cutt\$4 or cleav\$4) near10 (sheet or wafer) and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:33

S74	292	ingot near10 (cutt\$4 or cleav\$4) near10 (sheet or wafer) and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:33
S73	0	ingot near10 (cutt\$4 and cleav\$4) near10 (sheet or wafer) and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:33
S72	300	ingot near10 (cutt\$4 or cleav\$4) near10 (sheet or wafer) and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:33
S71	846	ingot near10 (cutt\$4 or cleav\$4) near10 (sheet or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:33
S70	2	"20040089222".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:33
S76	176	ingot near10 (cutt\$4 or cleav\$4) near10 (sheet or wafer) and @py<"1999" and semiconduct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:35
S77	65	ingot near10 (cutt\$4 or cleav\$4) near10 (sheet or wafer) and @py<"1999" and single near1 crystal\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:36
S80	0	ingot near10 (cutt\$5) near10 (sheet or wafer) same (gan or gallium near2 nitride) and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:38
S79	0	ingot near10 (cleav\$4) near10 (sheet or wafer) same (gan or gallium near2 nitride) and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:38
S78	6	ingot near10 (cleav\$4) near10 (sheet or wafer) and @py<"1999" and single near1 crystal\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:38

S81	5	ingot near10 (cutt\$5) near10 (sheet or wafer) same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:44
S83	46	S82 and sulfate near5 ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:45
S87	1452	429/223.ccls.	US-PGPUB; USPAT	OR	ON	2005/03/31 17:46
S85	20	S82 and sulfate near ion	US-PGPUB; USPAT	OR	ON	2005/03/31 17:46
S84	20	S82 and sulfate near ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:46
S82	1857	429/223.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:46
S90	20	S87 and sulfate near ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:47
S89	20	S87 and sulfate near ion	US-PGPUB; USPAT	OR	ON	2005/03/31 17:47
S88	20	S87 and sulfate near ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:47
S86	20	S82 and sulfate near ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:47
S91	11	S87 and sulfate near ion and lithium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:59
S92	54	(gan or gallium near2 nitride) near10 (hvpe or (halide or hydride) near5 vapor near2 epitax\$7) near10 (ingot or bulk)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 18:01

S93	19	(gan or gallium near2 nitride) near10 (hvpe or (halide or hydride) near5 vapor near2 epitax\$7) near10 (boule)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 18:31
S95	313	single near2 crystal\$6 near10 cleav\$6 near10 (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 18:32
S94	665	single near2 crystal\$6 near10 cleav\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 18:32
S96	41	semiconduct\$6 near4 single near2 crystal\$6 near10 cleav\$6 near10 (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 19:16
S97	17	("4727047" "6225650" "5843227" "5846609" "6087681" "6096130" "6156581").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 19:30
S98	477	(kensaku near2 motoki or takuji near2 okahisa or naoki near2 matsumoto).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 19:31
S99	36	S98 and mask\$5 same Gaas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 19:40
S10 1	2	"6013390".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 19:42
S10 0	2	"6693021".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 19:42